

**isc Silicon NPN Power Transistor**

**2SD388**

**DESCRIPTION**

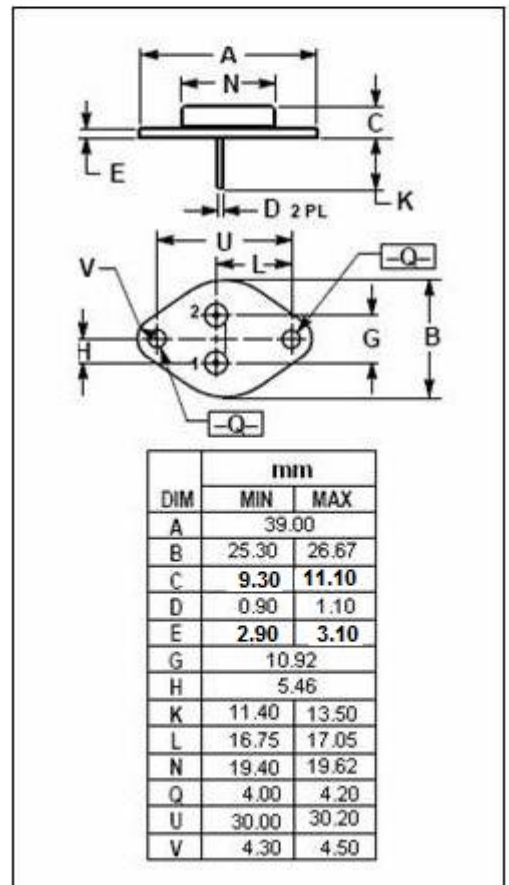
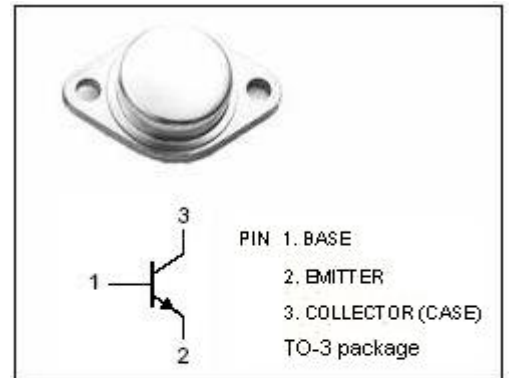
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 120V$  (Min)
- High Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for use in power amplifier and switching applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	MAX	UNIT
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	8	A
$I_{CM}$	Collector Current-Peak	12	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ C$	80	W
$T_j$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



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## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; R <sub>BE</sub> = ∞	120			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	150			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			0.8	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 150V; I <sub>E</sub> = 0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	60		320	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	20			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		9		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V, f <sub>test</sub> = 1MHz		190		pF

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